L Number	Hits	Search Text	LDD	I mi
1	26	5676587.pn. 5853604.uref. 5827781.uref.	DB USPAT;	Time stamp 2003/03/06 11:00
1	20	3070307.pm. 3033004.dref. 3027761.dref.	US-PGPUB	2003/03/00 11:00
2	2	5853604.pn. 5827781.pn.	USPAT;	2003/03/06 11:20
-		3033004.pm. 3027701.pm.	US-PGPUB	2003/03/00 11.20
3	5	("4193226"   "4811522"   "4963283"	USPAT	2003/03/06 11:02
		"5391258"   "5421769").PN.	OJIAI	2003/03/00 11:02
4	5	("3691694"   "5081421"   "5536202"	USPAT	2003/03/06 11:03
		"5643405"   "5733177").PN.	OSTAL	2003/03/00 11.03
5	8	5733177.uref.	USPAT;	2003/03/06 11:40
"			US-PGPUB	2003/03/00 11.40
6	5101	438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 11:42
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	2003/03/00 11.12
		451/41.ccls.	00 10105	
7	210	(438/626.ccls. 438/633.ccls.	USPAT;	2003/03/06 11:43
		438/687.ccls.) and (438/690.ccls.	US-PGPUB	2000,00,00 22010
		438/691.ccls. 438/692.ccls. 451/41.ccls.)		1
8	389	(438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 11:49
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
	!	451/41.ccls.) and (relative near2 (speed		
		velocity))		
10	2041	((cmp (chemical near mechanical)) with	EPO; JPO;	2003/03/06 11:50
		(copper cu conduct\$4 metal))	DERWENT;	
			IBM_TDB	
12	8908	((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 11:51
		(copper cu conduct\$4 metal))	US-PGPUB	
13	8	(((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 14:14
		(copper cu conduct\$4 metal))) same	US-PGPUB	
	00	(relative near2 (speed velocity))		0000/00/06 10 04
9	93	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls.	USPAT; US-PGPUB	2003/03/06 12:04
		438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	Ì
		near2 (speed velocity))) and ((cmp		
	:	(chemical near mechanical)) with (copper		
!		cu conduct\$4 metal))		
14	2	((438/626.ccls. 438/633.ccls.	USPAT;	2003/03/06 14:13
	_	438/687.ccls.) and (438/690.ccls.	US-PGPUB	
		438/691.ccls. 438/692.ccls. 451/41.ccls.))		
		and (relative near2 (speed velocity))		
15	14	(((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 14:21
		(copper cu conduct\$4 metal))) same	US-PGPUB	
		((relative linear) near2 (speed velocity))		1
16	16	(((cmp (chemical near mechanical)) with	USPAT;	2003/03/06 14:23
		(copper cu conduct\$4 metal))) same	US-PGPUB	
		((rotat\$6 near2 (speed velocity)) rpm		
		rpms) same (change decreas\$4 reduc\$5)	770	2002/02/06 14 20
11	3	(((cmp (chemical near mechanical)) with	EPO; JPO;	2003/03/06 14:38
	[ 1	(copper cu conduct\$4 metal))) and	DERWENT; IBM TDB	
17	1888	<pre>(relative near2 (speed velocity)) (cmp (chemical near mechanical) polish\$4)</pre>	USPAT;	2003/03/06 15:02
17	1000	and ((carrier head) same (retain\$4 ring	US-PGPUB	2003,03,00 13.02
		membrane)) and (wafer substrate) and	35 10100	
		(platen pad)		
18	505	(cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 15:03
		and ((carrier head) same (retain\$4 ring	US-PGPUB	
	[	membrane) same (platen pad) same (pressure		
		psi pa)) and (wafer substrate)		
19	501	(438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 14:49
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
		451/41.ccls.) and ((cmp (chemical near		
		mechanical) polish\$4) and ((carrier head)	A 1.	
		same (retain\$4 ring membrane)) and (wafer		
		substrate) and (platen pad))		10002/02/05
20	203	(438/626.ccls. 438/633.ccls. 438/687.ccls.	USPAT;	2003/03/06 14:49
. 1		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
i		451/41.ccls.) and ((cmp (chemical near		
		mechanical) polish\$4) and ((carrier head)		
		same (retain\$4 ring membrane) same (platen		
		<pre>pad) same (pressure psi pa)) and (wafer substrate))</pre>		1
		DUDDITUCE!!	L	L

22	787	((cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 14:54
	'6'	with (copper cu conduct\$4 metal)) and	US-PGPUB	2003/03/00 14:54
		((carrier head) same (retain\$4 ring	03-10100	
		membrane)) and (wafer substrate) and		]
		(platen pad)		i
23	231	((cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 14:57
		with (copper cu conduct\$4 metal)) and	US-PGPUB	2000/00/00 14.5/
		((carrier head) same (retain\$4 ring	00 10102	!
		membrane) same (platen pad) same (pressure	!	i I
l i		psi pa)) and (wafer substrate)		!
25	249	(cmp (chemical near mechanical) polish\$4)	EPO; JPO;	2003/03/06 15:02
	,	and ((carrier head) same (retain\$4 ring	DERWENT;	!
!   		membrane)) and (platen pad)	IBM_TDB	
21	83	(cmp (chemical near mechanical) polish\$4)	USPAT;	2003/03/06 15:04
		and ((carrier head) same (retain\$4 ring)	US-PGPUB	
		same membrane same (platen pad) same		
	7.50	(pressure psi pa)) and (wafer substrate)		
24	112	(	USPAT;	2003/03/06 16:00
		438/690.ccls. 438/691.ccls. 438/692.ccls.	US-PGPUB	
		451/41.ccls.) and (((cmp (chemical near		
		<pre>mechanical) polish\$4) with (copper cu conduct\$4 metal)) and ((carrier head) same</pre>		
		(retain\$4 ring membrane) same (platen pad)		
		same (pressure psi pa)) and (wafer		
		substrate))		
27	111	((cmp (chemical near mechanical) polish\$4)	EPO; JPO;	2003/03/06 17:01
_		and ((carrier head) same (retain\$4 ring	DERWENT;	
		membrane)) and (platen pad)) and (pressure	IBM TDB	
		psi pa copper cu metal conduct\$4)	_	
-	1	6204181.pn.	USPAT;	2003/03/06 09:48
			US-PGPUB	
-	1	20010004538.pn.	USPAT;	2003/03/05 17:55
			US-PGPUB	